IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kazutaka Yanagita et al.

Group Art Unit: to be assigned

Serial No.: to be assigned

Examiner: to be assigned

Filed: August 13, 2003

For: SAMPLE PROCESSING SYSTEM

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This Information Disclosure Statement is filed in accordance with 37 C.F.R. §§1.56, 1.97 and 1.98. The items listed on Form PTO-1449, a copy of which is not enclosed, are made of record to assist the Patent and Trademark Office in its examination of this application. The Examiner is respectfully requested to fully consider the items and to independently ascertain their teaching.

- For each of the following items listed on the enclosed copy of Form PTO-1449 that is not in the English language, an English language translation of that item or a portion thereof or a concise explanation of the relevance of that item is enclosed:
 For each of the following items listed on the enclosed copy of Form PTO-1449 that is not in the English language, a concise explanation of the relevance of that item is incorporated in the specification of the above-identified application.
- 3. Any copy of the items listed on the enclosed copy of Form PTO-1449 that is not enclosed with this Information Disclosure Statement was previously cited by or submitted to the Patent and Trademark Office in application Serial No. 10/153,608, filed May 24, 2002.

PATENT Attorney's Docket No. <u>1232-4590US2</u>

4. No fee is due under 37 C.F.R. §1.17(p) for this Information Disclosure Stat since it is being filed in compliance with:											
			37 C.F.R. §1.97(b)(1), within three months of the filing date of a national application other than a CPA; or								
			37 C.F.R. §1.97(b)(2), within three months of the date of entry into the national stage as set forth in §1.491 in an international application; or								
			37 C.F.R. §1.97(b)(3), before the mailing date of a first Office action on the merits; or								
			37 C.F.R. §1.97(b)(4) before the mailing date of a first office action after the filing of an RCE under §1.114.								
The Commissioner is hereby authorized to charge any additional fees which may be refor this Information Disclosure Statement, or credit any overpayment to Deposit Account. No. 13-4503, Order No. 1232-4590US2.											
			Respectfully submitted, MORGAN & FINNEGAN, L.L.P.								
Dat	ed: <u>A</u>	ugust 1	By: John A. Harroun Registration No. 46,339 (202) 857-7887 Telephone (202) 857-7929 Facsimile								
MC 345	ORGA Park	N & FI Avenue	Address: NNEGAN, L.L.P. 0154-0053								

Page 1 of 5 Attorney Docket: Serial No.: 1232-4590US2 to be assigned **FORM PTO-1449** Applicants: Examiner: Yanagita et al. to be assigned INFORMATION DISCLOSURE CITATION Filing Date: Group Art Unit: August 13, 2003 to be assigned U.S. PATENT DOCUMENTS Examiner **Publication** Sub-Initial **Patent Number** Date Name Class Class Filing Date AA3,493,155 02/03/70 Irving Litant et al. 2 225 AB3,549,446 12//22/70 R.W. Bennett et al. 156 230 AC 3,667,661 06/06/72 Farmer 225 2 AD 3,730,410 05/01/73 Altshuler 225 96.5 AE 4,962,879 10/16/90 Goesele et al. 156 281X AF 03/31/92 5,100,544 Izutani, et al. 210 75 AG 5,255,853 10/26/93 Munoz 83 177X AH 5,374,564 12/20/94 Bruel 437 24 01/03/95 ΑI 5,379,235 Fisher et al. 364 508 FOREIGN PATENT DOCUMENTS Examiner **Publication** Sub-Initial **Patent Number** Date Country Class Class Translation 0/75/98 AJ KR 1998-33377 Korean ☐ Yes ☐ No ΑK EP 0 709 876 A1 05/01/96 Europe ☐ Yes ☐ No ΑL EP 0 840 381 A2 05/06/98 Europe EP 0 843 345 A2 AM 5/20/98 Europe ☐ Yes ☐ No OTHER DOCUMENTS (Including Author, Title, Date, etc.) "Single-Crystal Silicon on Non-Single-Crystal Insulators", G.W. Cullen, Journal of Crystal Growth, Vol. 63, AN No. 3, pp. 429-590, 1983 "Crystalline Quality of Silicon Layer Formed by FIPOS Technology", Kazuo IMAI et al., Journal of Crystal AO Growth, Vol. 63, pp 547-553, 1987 "Silicon-On-Insulator by Wafer Bonding: A Review", W.P. Maszara, Journal of Electrochemical Society, Vol. AP 138, pp. 341-347, 1991 Examiner Date Considered

Initial if reference considered, whether or not citation is in conformance with MPEP §609.

Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

EXAMINER:

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Attorney Docket:	Serial No.:
1232-4590US2	to be assigned
Applicants	Examiner:
Yanagita et al.	to be assigned
Filing Date:	Group Art Unit:
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	CX	JPA63-16455	11/15/94		Japan			Abstract
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